

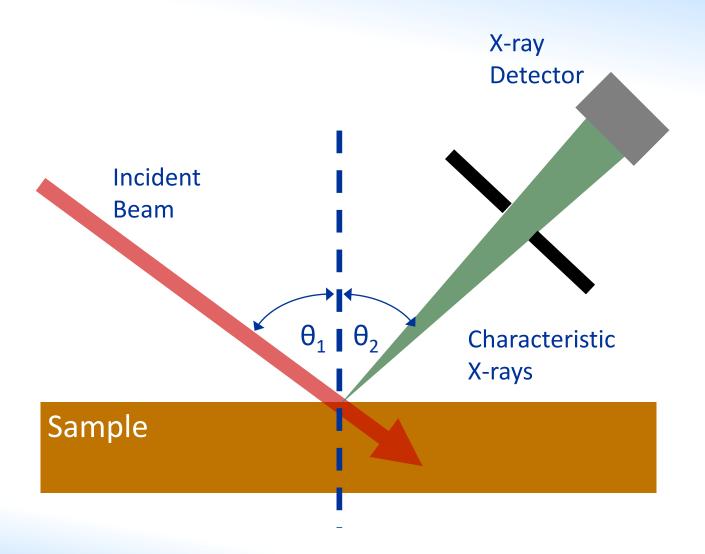
XRF techniques for materials and life sciences

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Nuclear Science and Instrumentation Laboratory International Atomic Energy Agency

Conventional XRF





Sources of ionizing radiation



- Electrons (SEM)
- Charged particles (accelerators)
- Radioisotopes (α, γ, X-rays)
- X-ray Tubes
- Synchrotron radiation

Interaction of X-rays with matter



X-rays can interact with the atoms of the material in two different ways:

• <u>Photoelectric effect</u>: Primary X-ray radiation can ionise atoms of the material. The X-ray is absorbed in this process

Scattering:

- Elastic/Coherent scattering (Rayleigh): no energy loss after collision with electrons. The Rayleigh effect is present when electrons are strongly bound (inner atomic electrons)
- Inelastic/Incoherent scattering (Compton): energy loss after collision with electrons. The Compton effect is present when electrons are loosely bound (outer, less bound electrons)

Photoelectric effect

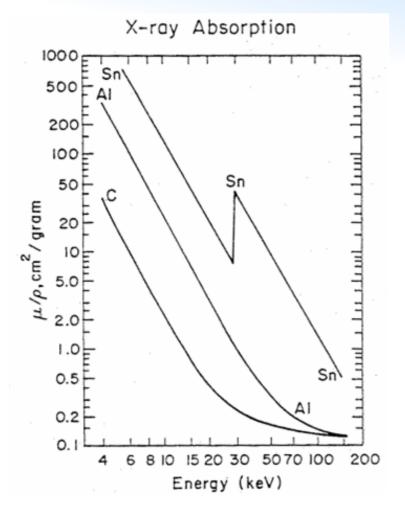


Photoelectric effect: Primary X-ray radiation can ionise atoms of the material to be analysed

Cross section of the PE depends strongly on Z of the material and on the energy of the primary X-ray

$$\sigma_{Ph} \propto \frac{Z^n}{E_X^{3.5}}$$
 $n = 3 \div 4$

To maximize the ionization probability, the energy of the primary X-ray should be higher than the binding energy but as close as possible to it



□ X-Ray Fluorescence



Incident photon Energy E_0 should be adequate to ionize the atomic bound electrons $\rightarrow E_0 \ge$ inner shell binding energy

Fluorescence X-ray emission is **isotropic**

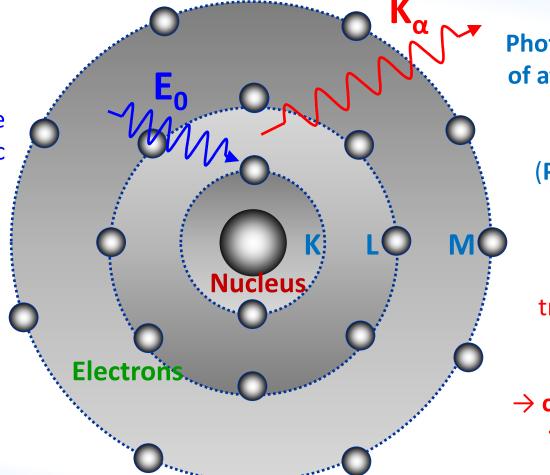
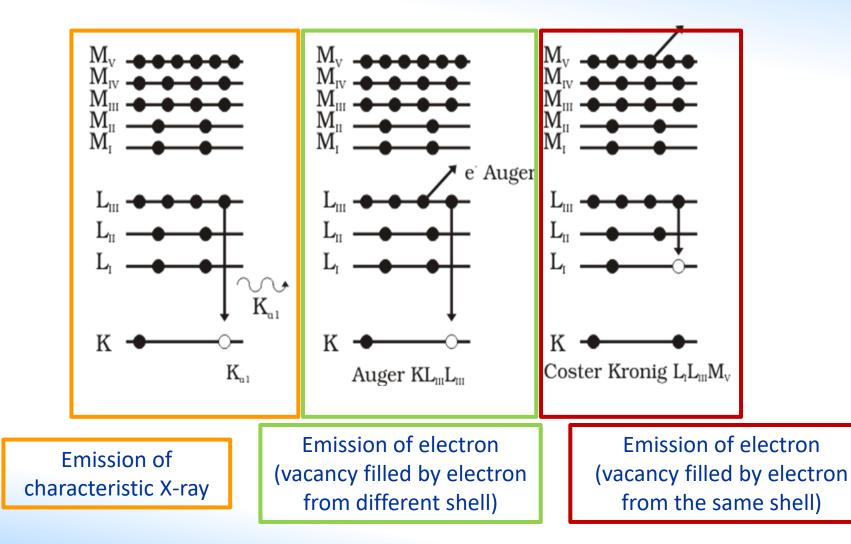


Photo-Ionization of atomic bound electrons (K, L, M) (Photoelectric absorption)

Electronic transition and emission of element → characteristic fluorescence radiation

De-excitation: Fluorescence/Auger

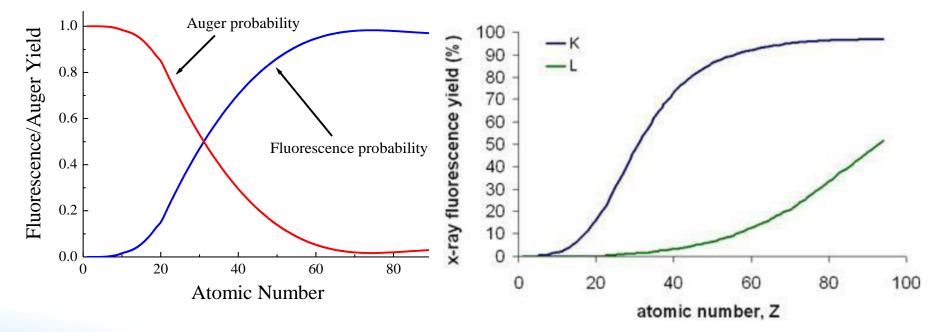




Fluorescence yield



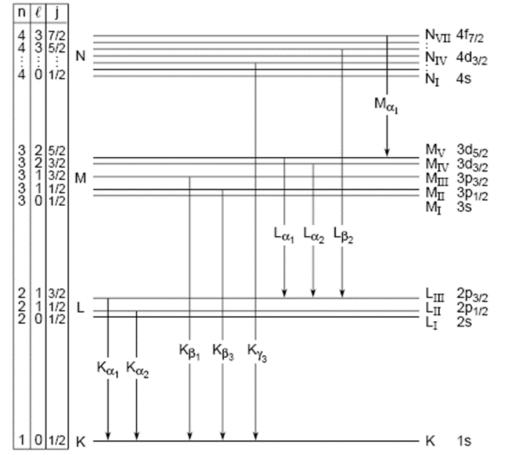
The fluorescence yield is given by the **ratio of the emitted fluorescence photons over the number of the created holes**. The competing process is the **emission of Auger electrons** as the atom returns to its ground state



For low Z the Auger electron emission is dominant

Emission of characteristic X-rays





The emission of characteristic X-ray lines follows allowed electronic transitions between specific subshells

Each element has a unique set of emission lines

Siegbahn/IUPAC notation:

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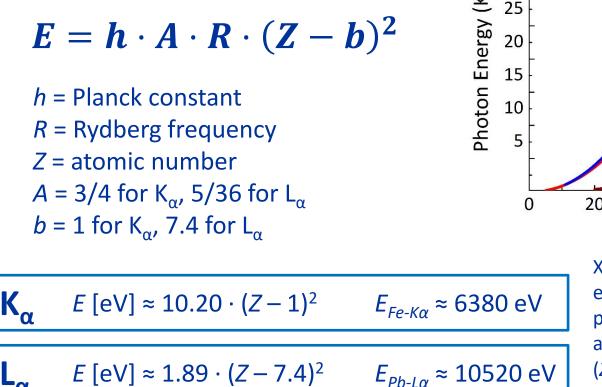
$$\mathbf{K}_{\alpha}$$
: K-L₂ + K-L₃
 \mathbf{K}_{β} : K-M₂ + K-M₃
 \mathbf{L}_{α} : L₃-M₄ + L₃-M₅
 $\mathbf{L}_{\beta 1}$: L₂-M₄
 $\mathbf{L}_{\beta 2}$: L₃-N₅

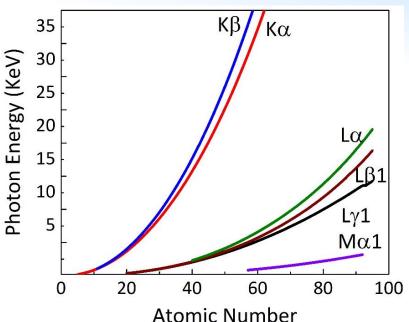
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Moseley's law



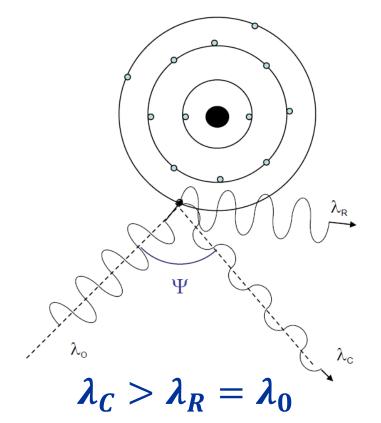


X-ray spectroscopy within the energy range $1\div30$ keV offers in principle the possibility to detect all the periodic table elements (Z > 10) through their K, L or even M series of emission lines



X-ray scattering





Elastic/coherent scattering (Rayleigh):

no energy loss after collision with electrons. The Rayleigh effect is present when electrons are strongly bound.

<u>Rayleigh is more intense for high Z (= heavy)</u> <u>matrices</u>

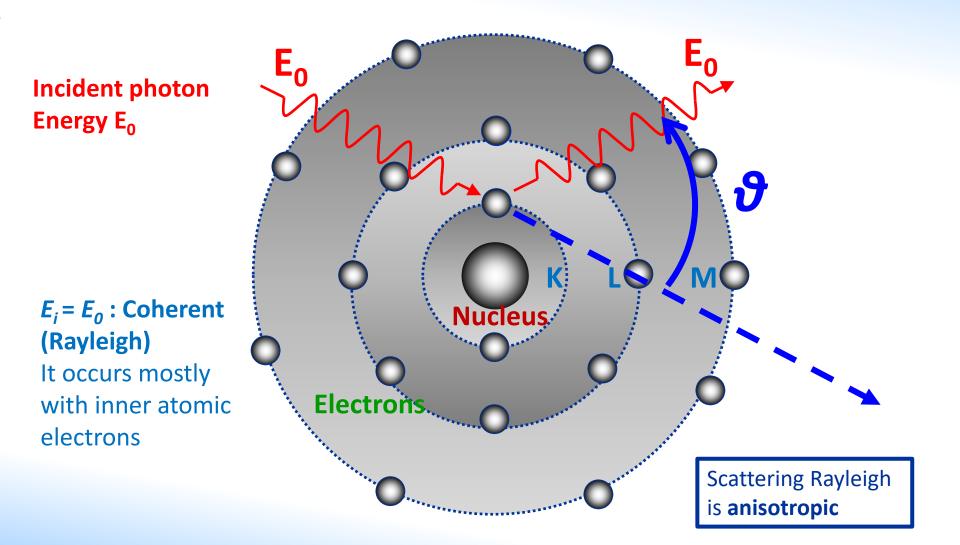
Inelastic/Incoherent scattering (Compton):

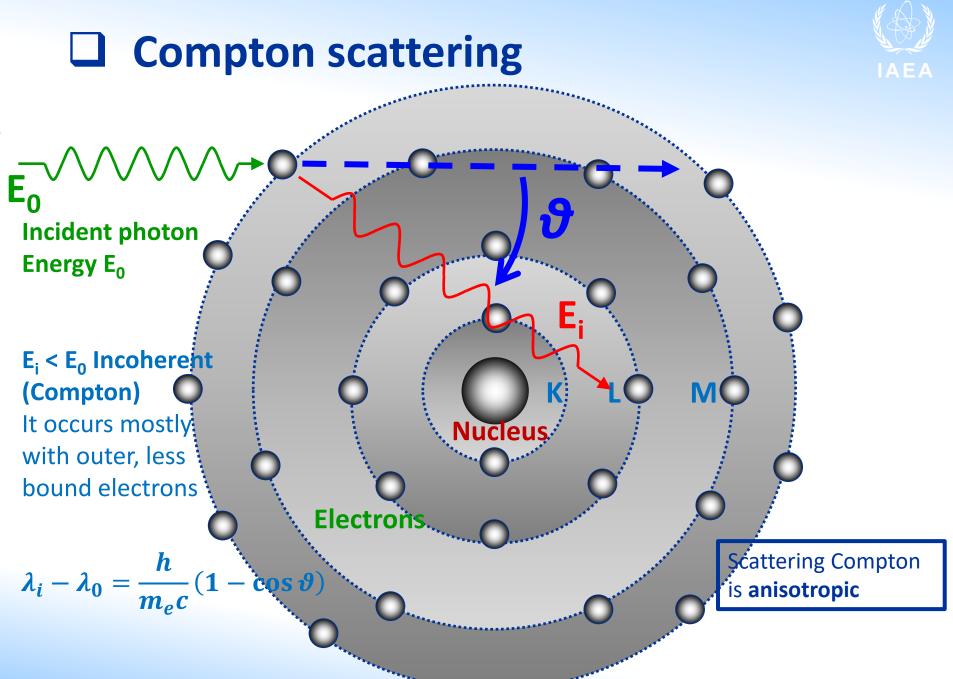
energy loss after collision with electrons. The Compton effect is present when electrons are loosely bound.

<u>Compton is more intense for low Z (= light)</u> <u>matrices</u>

Rayleigh scattering

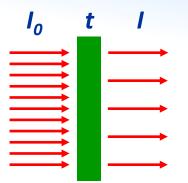






Linear attenuation coefficient μ





Attenuation of photons by a thin layer of thickness *dt* is described by

 $dI = I \cdot \mu \cdot dt$

where *I* is the number of photons per unit area and unit time (photon flux) of which *dI* are attenuated while penetrating the layer of a material characterized by the (**total, linear**) **attenuation coefficient** μ . This is equivalent to

$$I=I_0\cdot e^{-\mu\cdot t}$$

I and I_0 are the photon fluxes behind and in front of the absorber, respectively, and *t* is the thickness. μ is a function not only of the material (atomic number *Z*) but also of the photon energy *E*

D Mass attenuation coefficient μ_m



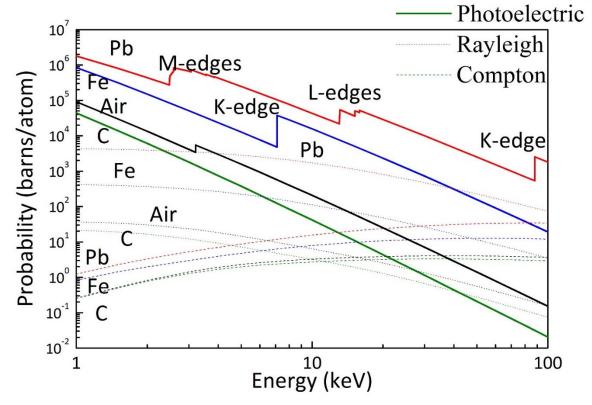
$$\boldsymbol{\mu} = \boldsymbol{\mu}_m \cdot \boldsymbol{\rho}$$

the total mass attenuation coefficient μ_m doesn't depend on the density ρ of the material. The coefficient μ_m summarizes all possible photon interactions

$$\mu_m = \tau_m + \sigma_m$$

where τ_m describes the photo absorption and $\sigma_m = \sigma_{coh} + \sigma_{inc}$ are the contributions by coherent and incoherent scattering, respectively.

Both kinds of scattering contribute much less than the photo absorption to the total μ_m



D Mass attenuation coefficient μ_m



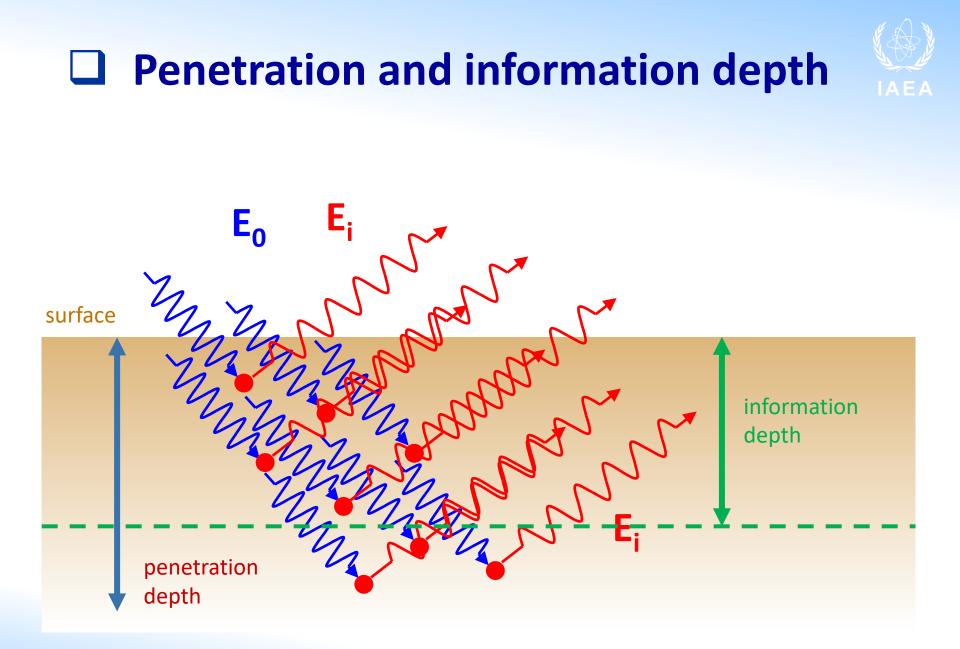
the mass attenuation coefficient of a material that is <u>composed of</u> <u>several elements</u>, with weight fractions w_i , is

$$\mu_m = \sum_i w_i \cdot \mu_m^i$$

Use of mass attenuation coefficients suggests replacing the thickness by the **area-related mass** m = M/A (mass M per unit area A) and rewriting the attenuation law as

$$I=I_0\cdot e^{-\mu_m\cdot m}$$

 $t \cdot \rho = M/A$, in grams/cm²

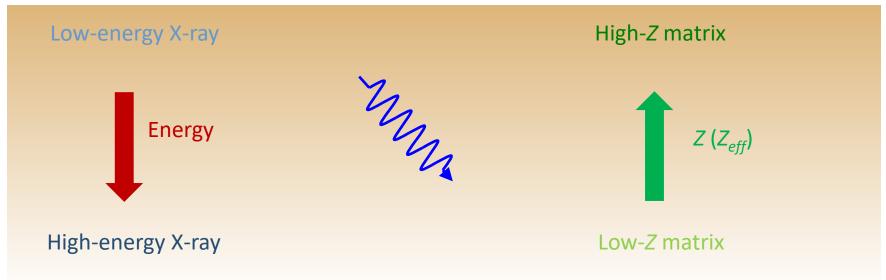


Penetration and information depth

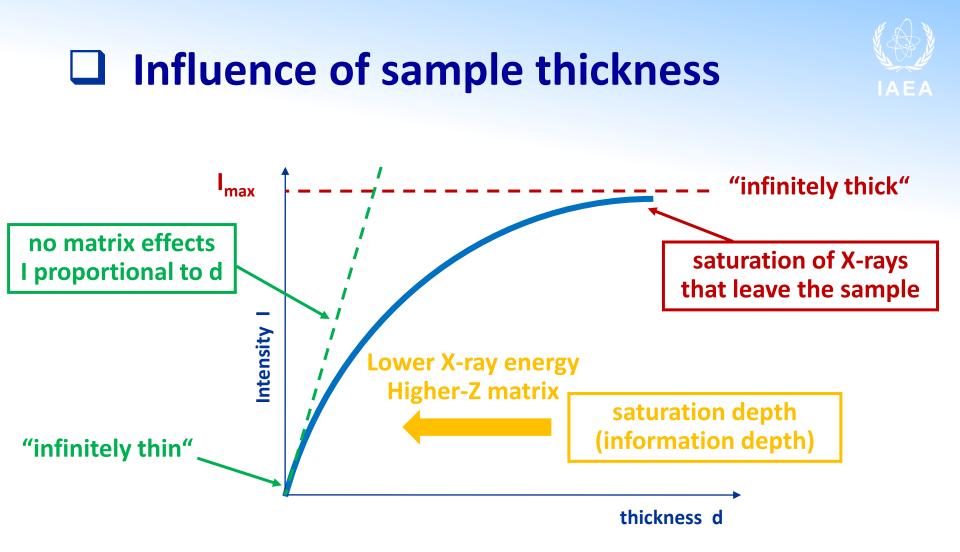


Penetration and information (analytical) depth depend on the energy of the X-ray and on the matrix:

surface



- Surface treatment is extremely important for heavy matrices
- Information thickness is essential for light matrices



Increasing the thickness of the sample above the information depth will not increase the signal but only the scattering of the primary radiation

Analytical depths in different matrices

Different elements exhibit different Information thicknesses (99%), depending on their characteristic X-ray energy and on the overall matrix

Line	Energy	Graphite	Glass	Iron	Lead
Cd K _{a1}	23,17 keV	14,46 cm	8,20 mm	0,70 mm	77,30 μm
Μο Κ α1	17,48	6,06	3,60	0,31	36,70
Cu K α1	8,05	5,51 mm	0,38	36,40 μm	20,00
Ni K α1	7,48	4,39	0,31	29,80	16,60
Fe K _{α1}	6,40	2,72	0,20	*164,00	11,10
Cr K _{α1}	5,41	1,62	0,12	104,00	7,23
S K α1	2,31	116,00 μm	14,80 μm	10,10	4,83
Mg K _{α1}	1,25	20,00	7,08	1,92	1,13
F K α1	0,68	3,70	1,71	0,36	0,26
Ν Κ α1	0,39	0,83	1,11	0,08	0,07
C K α1	0,28	*13,60	0,42	0,03	0,03
Β Κ α1	0,18	4,19	0,13	0,01	0,01

E_{KC} = 0.2842

E_{KFe} = **7.112**

Detectors

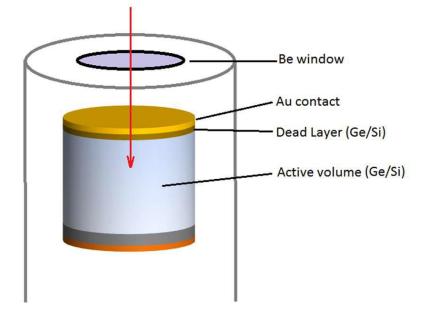


- Proportional Counters
- Scintillation Detectors
- Si(Li)
- LEGe
- PIN Diode
- <u>SDD</u>
- CCD, CMOS cameras
- CZT, other

Semiconductor detectors



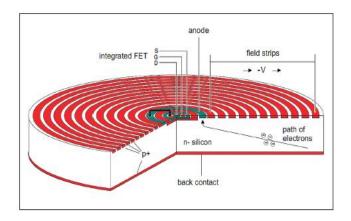
- X-rays produce electron-hole pairs, whose number is proportional to the energy of the radiation (average energy to produce an electron/hole pair is 3.6eV for Si and 2.9eV for Ge)
- Electrons and holes are collected from the depleted active region to the electrodes, where they result in a pulse that can be further amplified and finally measured
- This pulse carries information about the energy of the original incident radiation. The number of such pulses per unit time also gives information about the intensity of the radiation



Silicon Drift Detectors - SDD



The charge is drifted from a large area into a small read-out node with low capacitance, independent of the active area of the sensor. Thus, the serial noise decreases, and shorter shaping time can be used. For SDDs faster counting is enabled and higher leakage current can be accepted, drastically reducing the need for cooling.



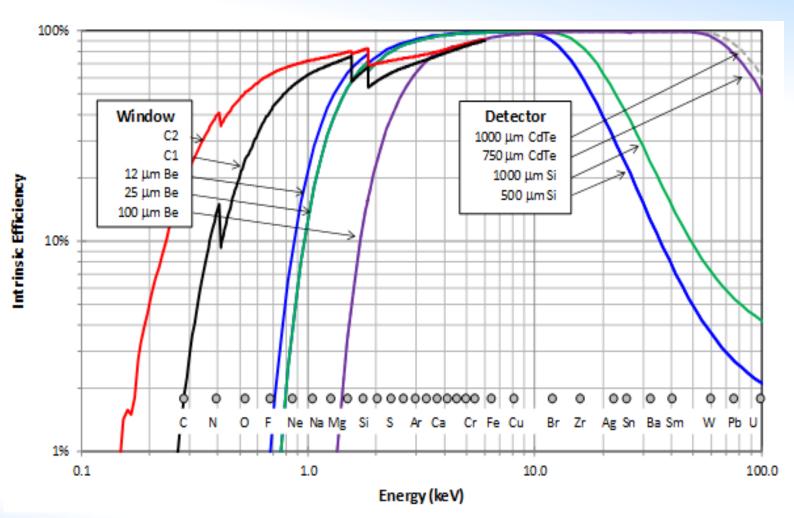
- Energy resolution ~ 125 140 eV (Mn-Ka)
- Input capability ~ 10⁶ photons/sec

https://tools.thermofisher.com/content/sfs/bro chures/TN52342_E_0512M_SiliconDrift_H.pdf



Detector photograph reproduced from https://www.rayspec.co.uk/x-ray-detectors/silicondrift-detectors/xrf/

Efficiencies of different detectors

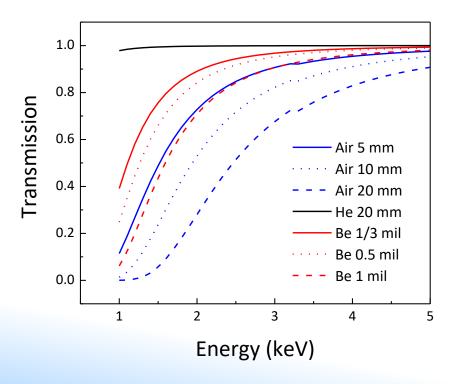


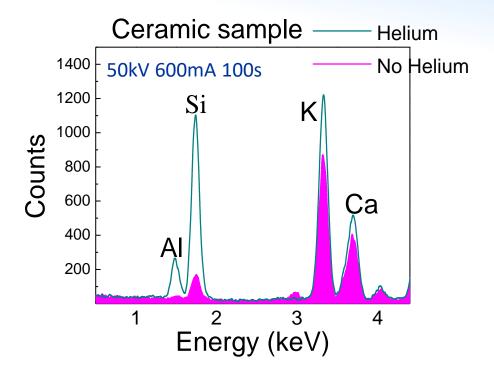
Comparison of different detector's efficiency from AMPTEK https://www.amptek.com/products/x-ray-detectors/fastsdd-x-ray-detectorsfor-xrf-eds/fastsdd-silicon-drift-detector

"Light" elements (Na, Mg, Al, Si)



Vacuum atmosphere or **He flushing** is required in the x-rays path between sample and detector



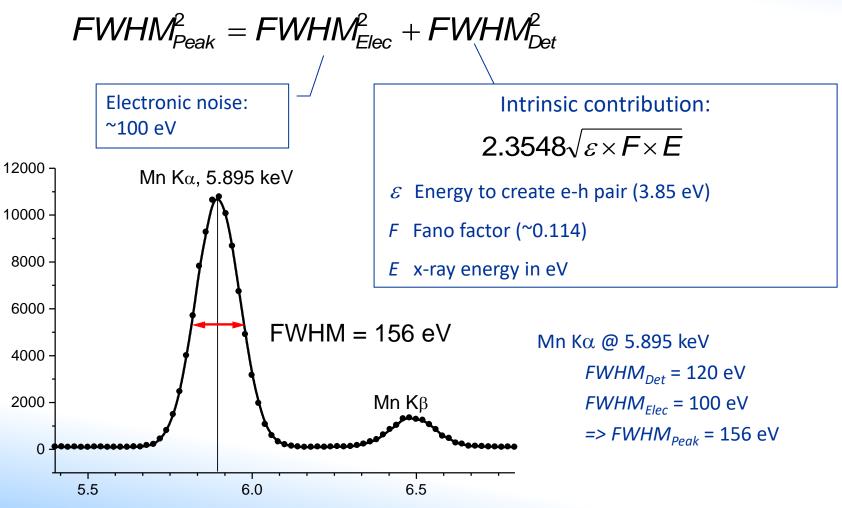


The improvement in the intensity of Al-K and Si-K characteristic X-ray lines is significant, 22 and 7.3 times respectively

Typical EDXRF spectrum Escape peaks (Ca-Ka - 1.74 keV = 1.95 keV) Characteristic radiation Trais Drayne Sehip Window I 이 씨와 지난도 저희 도접 이번들을 받았 ✓ K, L or M-lines Sqrt(Counts) 48 42 Са 36 **Scatter** 30 ✓ Coherent 24 18 ✓ Incoherent 12 6 18)00 1 I 16 17 10 11 12 13 14 15 8 9 Energy (keV) Sum peaks Fe-Ka + Fe-Ka= 12.8 keV **Continuum radiation**

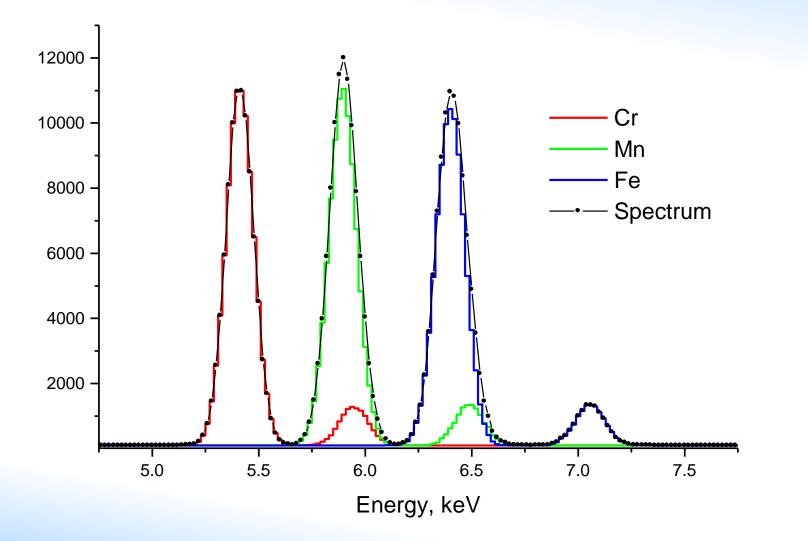
Resolution of EDXRF spectrometers

Full Width at Half Maximum (FWHM) of a peak



sEnergy, SeVhrotron Light Sources and their Applications, 13-24 January 2025





Case of strong overlapping



Overlapping of As-Kα (about 10.54 keV) and Pb-Lα lines (about 10.55 keV)

Binding energies:

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As-K = 11.87keV
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Pb-L₃ = 13.04keV Pb-L₂ = 15.20keV Pb-L₁ = 15.86keV

Arsenic can be easily quantified at synchrotron using an energy 11.87 keV < E < 13.04 keV

The Shermann-Nikina formulae



$$I_i = \varepsilon (E_i) w_i \int_{E > E_i^{ab}}^{E_{\text{max}}} GK_i A(E_0, E_i) R_i (E_0, E_j) I_0(E_0) dE_0$$

 $K_{i} = \frac{J_{K}^{i} - 1}{J_{K}^{i}} \omega_{K}^{i} f_{K_{\alpha}}^{i} \tau_{i}(E_{0})$ $A_{S}(E_{0}, E_{i}) = \frac{1 - e^{-\chi_{S}(E_{0}, E_{i})\rho x}}{\chi_{S}(E_{0}, E_{i})}$

Contains all the fundamental parameters for specific k-line of element *i*

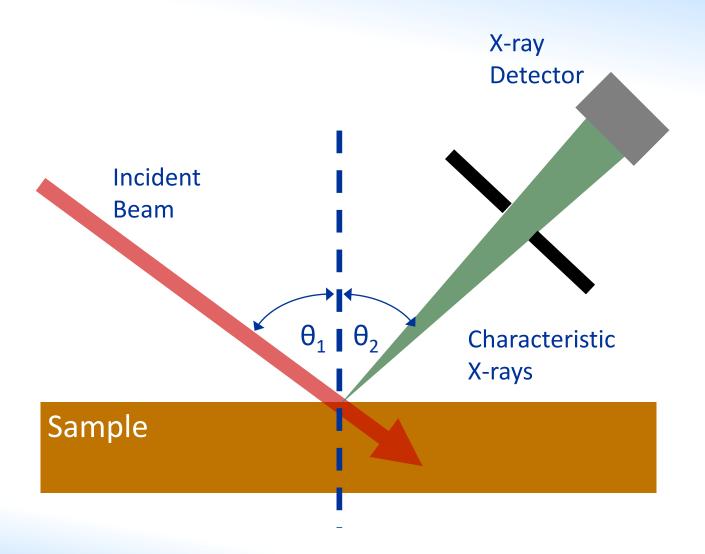
Takes into account the attenuation of both excitation and fluorescent radiation in the sample

 $R_i(E_0, E_j)$ Considers the enhancement of x-ray production of element *i* by the characteristic of other major elements *j* present in the sample and having characteristic energies larger than absorption edge of element *i*

- $I_0(E_0)$ Is the probability distribution by energies of the excitation radiation
- $\varepsilon(E_i)$ Is the efficiency of the detector for energy E_i
- *G* Is the overall effective solid angle for excitation and detection

Conventional XRF

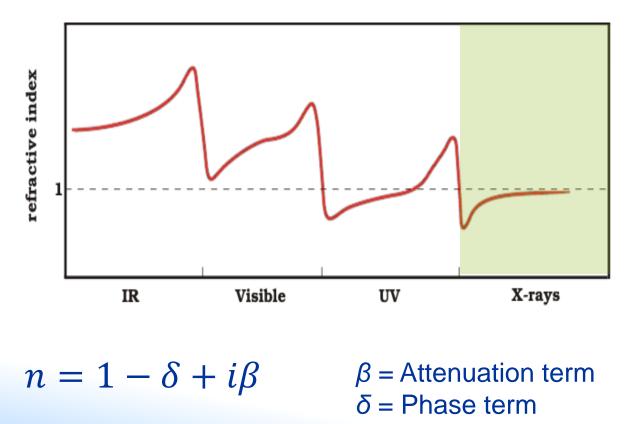




X-ray optics

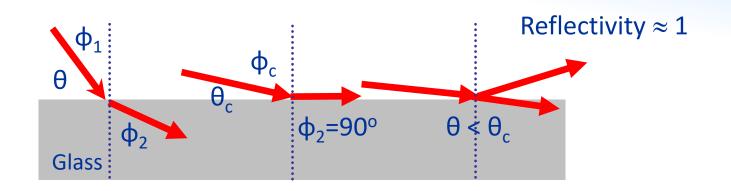






□ X-ray total reflection

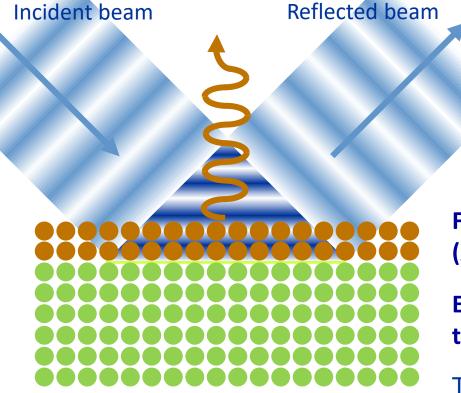




$$\begin{aligned} \text{Snell Law} \quad & \frac{\sin \phi_2}{\sin \phi_1} = \frac{1}{n} \quad \Rightarrow \quad \sin \phi_2 = \frac{\sin \phi_1}{n} \quad \Rightarrow \quad \phi_2 > \phi_1 \qquad n \approx 1 - \delta \\ \\ \vartheta_{crit} = \sqrt{2\delta} \qquad & \vartheta_{crit}(deg) \approx \frac{1.651}{E(keV)} \sqrt{\frac{Z}{A}\rho(\frac{g}{cm^3})} \qquad & Z: \text{Atomic number} \\ A: \text{Atomic mass} \\ \rho: \text{Density} \end{aligned}$$

X-ray Standing Wave





Formation of X-ray Standing Wave (XSW) at grazing incident/exit angle

Electric Field Modulations above the surface

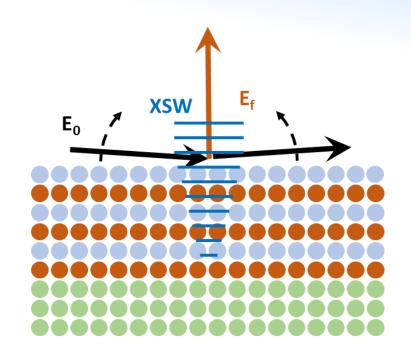
The X-ray fluorescence intensity from the sample depends on the varying field intensity of the XSW field within the sample

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GIXRF and XRR

By varying continuously the grazing incident angle through and few times above the critical angle for TR, the recorded XRF intensity profiles (Grazing Incidence-XRF analysis) have the potential to provide information on structural and compositional properties of thin films, such as the layer composition, sequence, thicknesses and densities, interface roughness, in depth elemental gradients of matrix elements or dopants in semiconductors, characterization of nano-particles deposited on flat surfaces, etc

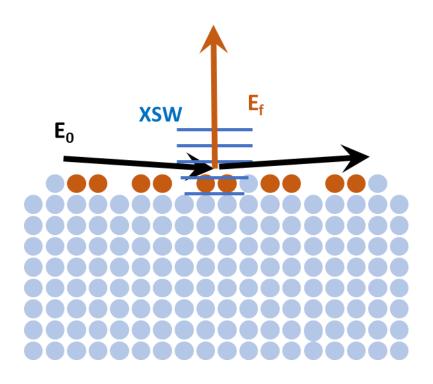
A more accurate and robust reconstruction of these thin film properties requires the synergy or even the simultaneous fitting of GI-XRF with X-ray reflectometry (XRR) data





Total reflection X-ray Fluorescence





TXRF is essentially an energy dispersive XRF technique arranged in a special geometry.

Due to this configuration, the measured spectral background in TXRF is less than in conventional XRF. This reduction results in increased signal to noise ratio.

TXRF is a surface elemental analysis technique often used for the ultra-trace analysis of particles, residues, and impurities on smooth surfaces.



The joint IAEA-Elettra XRF beamline at Elettra Sincrotrone Trieste

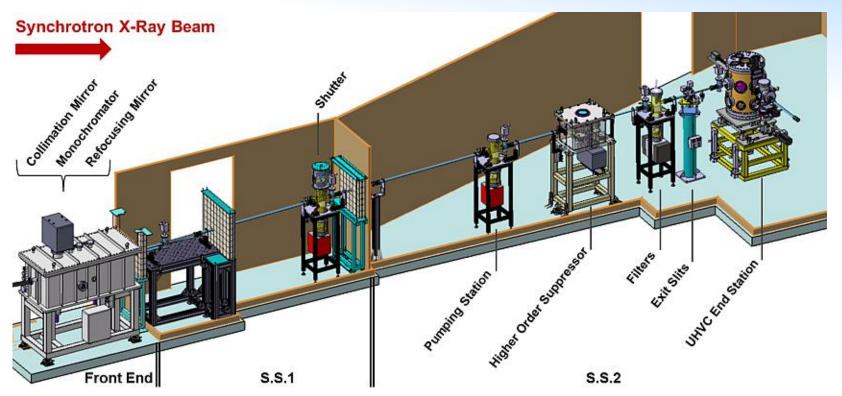


Elettra Sincrotrone Trieste



Optical layout



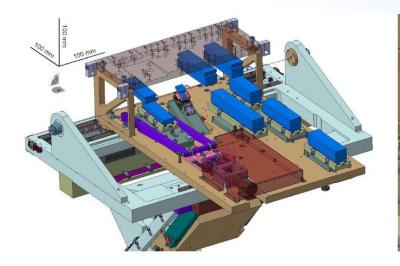


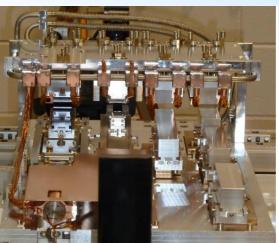
Source	Bending magnet	
Flux	10 ¹⁰ ph/s (at 5 keV for 2.0 GeV, at 10 keV for 2.4 GeV) (Si 111)	
Spot size	250 x 100 (H x V) μm²	
Beam divergence	< 0.15 mrad (at exit slits)	

Werner Jark, Diane Eichert, Lars Luehl, Alessandro Gambitta, *Optimisation of a compact optical system for the beam transport at the x-ray fluorescence beamline at Elettra for experiments with small spots*, Proc. SPIE 9207, Advances in X-Ray/EUV Optics and Components IX, 92070G, 2014; doi: 10.1117/12.2063009

The monochromator at XRF





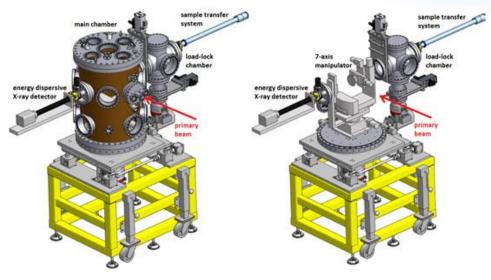


Optics type	E range (keV)	E resolution (∆E)
Si(111)	3.6 - 14	~ 1 eV at 7 keV
InSb(111)	2.0 - 3.8	~ 1eV at 2.2 keV
ML: High E (RuB ₄ C)	4.0 - 14.0	~ 55 eV at 1 keV ~ 180 eV at 14 keV
ML: Medium E (NiC)	1.5 - 8.0	
ML: Low E (RuB ₄ C)	0.7 – 1.8	

Werner Jark et al., Proc. SPIE 9207, Advances in X-Ray/EUV Optics and Components IX, 92070G, 2014; doi: 10.1117/12.2063009

IAEAXspe endstation





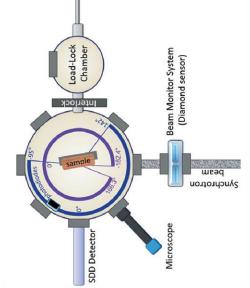


The IAEA end-station is based on a prototype design by Physikalisch - Technische Bundesanstalt (PTB, Berlin) and Technical University of Berlin (TUB)

Available detectors:

- Diamond detector for I₀
- SDD detector for XRF (different variants) and XAS (in fluorescence geometry)
- Photodiodes for **XAS** in transmission geometry
- Photodiodes with 100 and 200µm slits and SDD for XRR

Andreas G. Karydas et al., J. Synchrotron Rad. (2018). 25, 189–203



7-Axis Manipulator

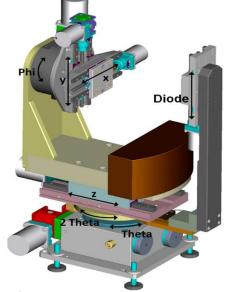


Sample arm

- 3 linear stages (X, Y, Z)
- 2 goniometers (Theta, Phi) Photodiodes arm:
- 1 linear stages (diode)
- 1 goniometer (2Theta)



- Sample can be moved in various directions/ orientations with respect to the exciting Xray beam or with respect to the detectors.
- Ultra Thin Window (UTW) Bruker Silicon Drift detector (30 mm², FWHM 131 eV @ Mn-Ka), Si photodiodes



Full step resolution Linear axes: Diode, X, Y, Z (0.005mm, 0.005mm, 0.0005mm, 0.01mm) Goniometers: Theta, 2theta, phi (0.001°, 0.001°, 0.005°)

Environmental monitoring (air particulate matter, water)

- Biological: Elemental distribution/ speciation on plant organ (leaves, roots, shoots, seeds, etc.)
- Cultural Heritage preventive conservation

Materials Science: Structured materials for

energy storage and conversion technologies

Nanomedicine - Biosensing technologies

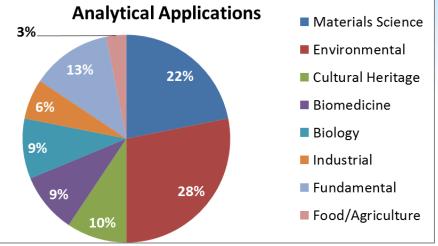
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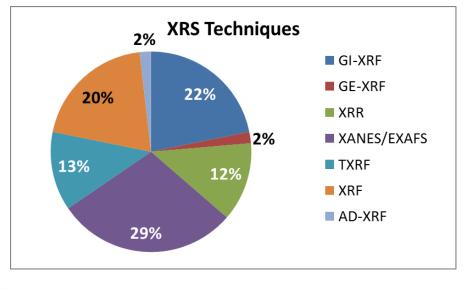
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- Food products security Authenticity
- Determination of X-Ray Fundamental Parameters

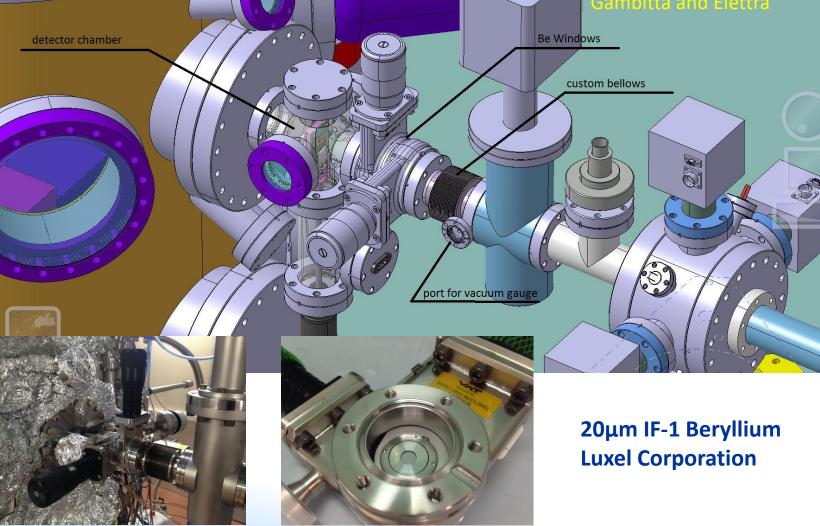






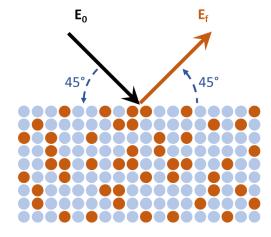
non-UHV compatible samples



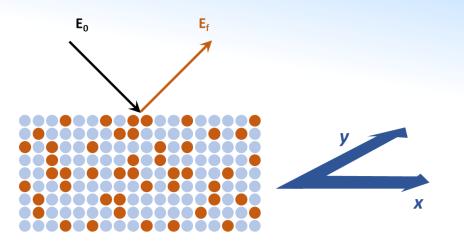


Geometries and techniques





Standard 45°/45° - XRF



micro - XRF

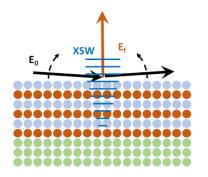




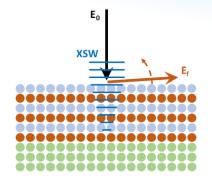
X-ray Absorption Spectroscopy (on hot spots)

Grazing angle geometries

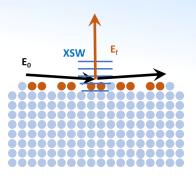




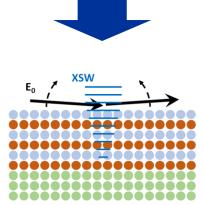
Grazing Incident - XRF



Grazing Emission - XRF



Total reflection - XRF



X-Ray Reflectometry

Depth profiling measurements

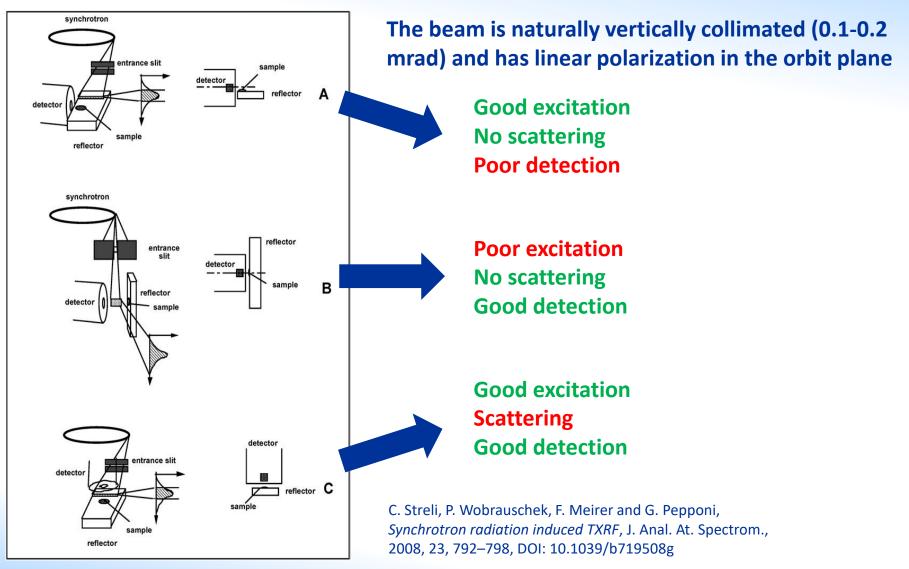
Trace element analysis Surface contamination



X-ray Absorption Spectroscopy (in TXRF geometry)

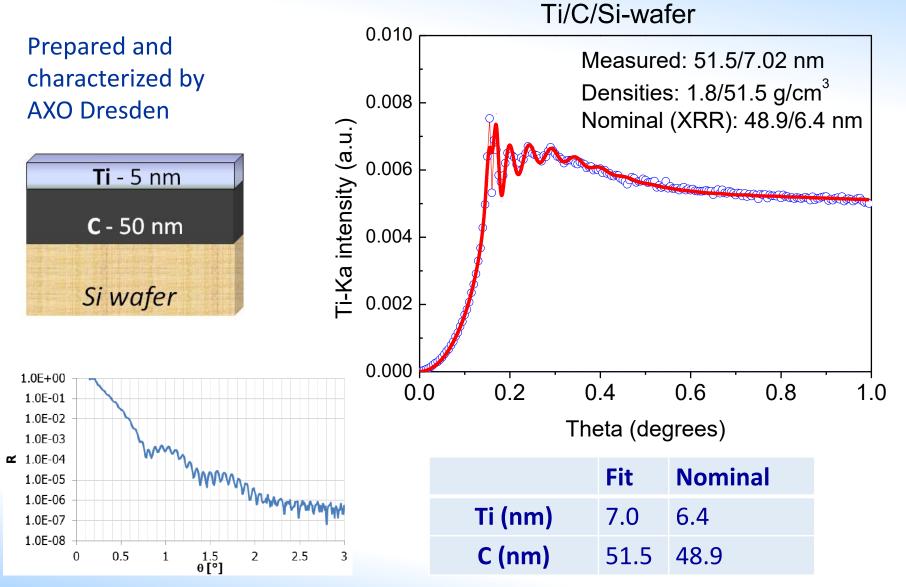
Detector geometry for TXRF





GIXRF: C/Ti double layer

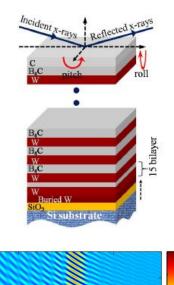


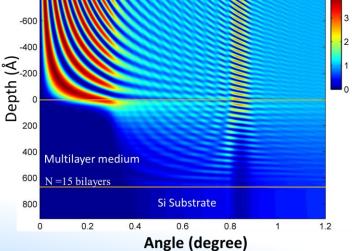


□ W/B₄C multilayered (x15) thin film

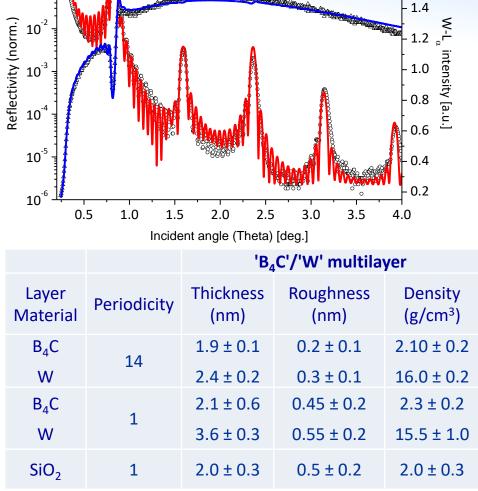
10⁻¹ ·

Multilayered sample, prepared by the Ramanna Center for Advanced Technology, Indore, India





Electric Field Intensity (Normalized)



1.8

1.6

• XRR

GIXRF

good agreement with previous analyses performed at the BL-16 beamline of Indus II

Zn speciation in fractionated APM

9-stage Maytype cascade impactor

Sampling of size fractionated aerosol, down to 0.07um size 20-3200 L of air



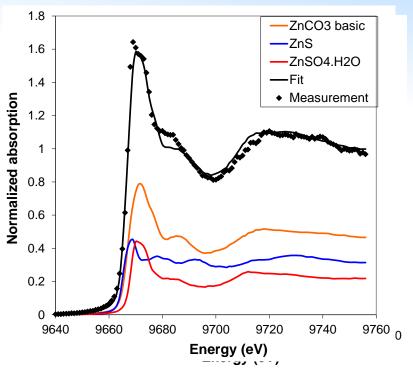
Deposited particles form a stripe of 200-500 μ m width on the 20x20 mm² Si wafer



Sample geometry well suited to SR-TXRF-XANES investigations!

J. Osan, Environmental Physics Department, Centre for Energy Research, Budapest, Hungary

*Self-absorption correction as described in: Osán J et *al.*, Spectrochim Acta Part B 65 (2010) 1008-1013



Semplete PBkst (Hpuese (HPV)n ga3y)). 6. μ5-,0.3 μm, Zzrcooteett: 7.2398 /g)3-628824 ng on 20 mm stripp)

38%ZZAAOO, 492%ZZNAS, 222%ZZnimegaas**

Main Bouree In angle painted wood

Aerosols from 3D metal printing



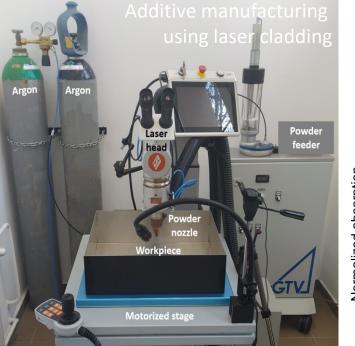
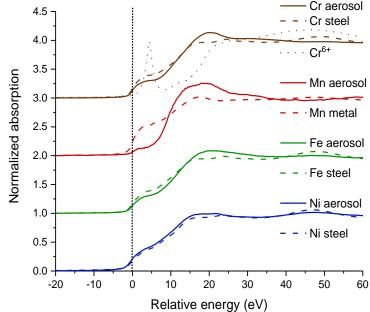


Figure courtesy: Attila Nagy, Wigner FK, Budapest, Hungary

XANES: Elettra XRF and XAFS beamlines

Cr oxidized – oxidation number \sim +1.0 No significant amount of Cr⁶⁺ detected



Mn mostly oxidized – oxidation number ~+2.3

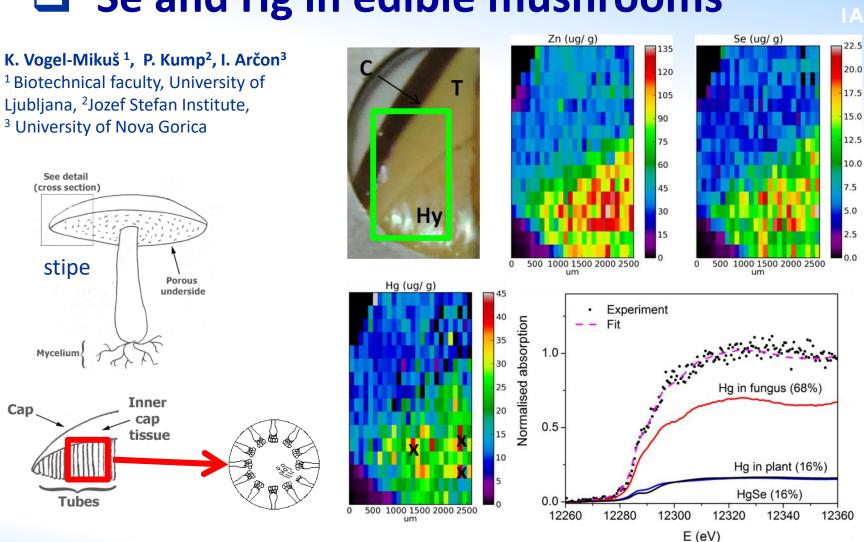
Fe slightly oxidized – oxidation number ~+0.7

Ni mostly metallic – oxidation number ~+0.1

Most of emitted aerosol particles are in the ultrafine range

Oxidation number increases with decreasing particle diameter – important for estimation of health effects

S. Kugler et al., Spectrochim. Acta Part B 2021, 177, 106110



Hg is bound to tetra-cysteine proteins (metallothioneins). These proteins are digested by enzyms in the stomach and Hg is released and absorbed in our body.

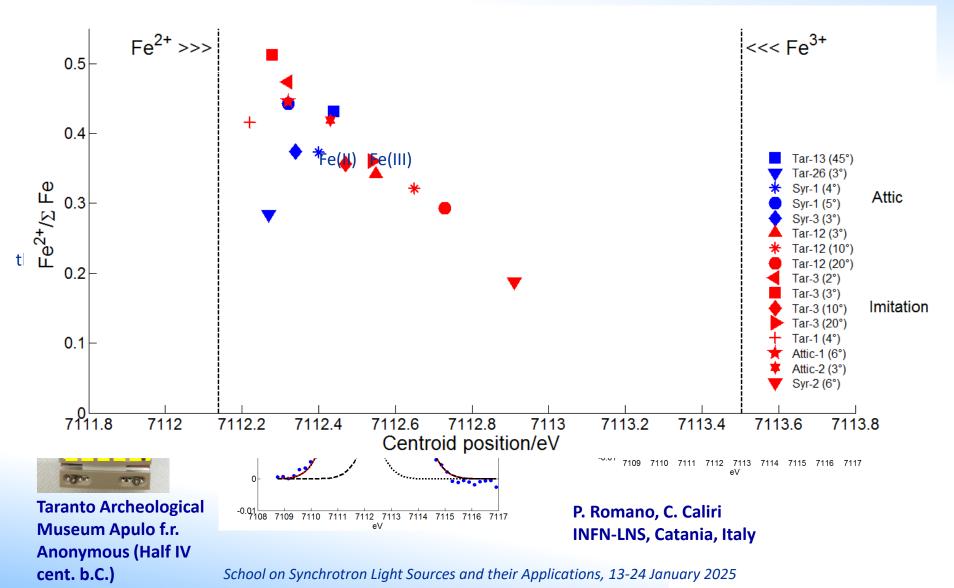
School on Synchrotron Light Sources and their Applications, 13-24 January 2025

Se and Hg in edible mushrooms

GI-XANES on Black Glaze



Fe-based decorations of Ancient ceramics manufactured in South Italy



Analysis of gold samples

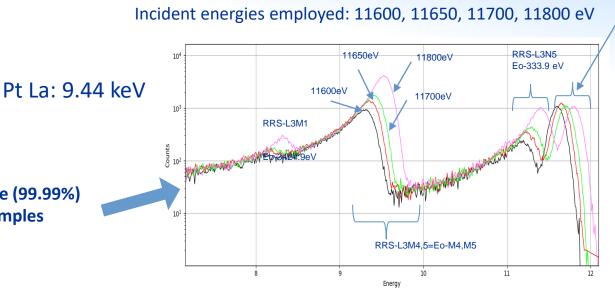


Eo elastic scattering

Absorption edges of Pt and Au

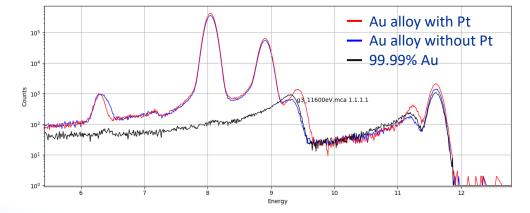
	Pt	Au
Z	78	79
L1 (keV)	13.88	14.353
L2 (keV)	13.273	13.734
L3 (keV)	11.564	11.919

Synchrotron XRF spectra of pure (99.99%) thick (thickness 25 µm) gold samples



Eo=11600 eV @Elettra

Pure gold spectrum vs. Gold alloy with 0.15% Pt (Au:65.56%, Cu:25.21%, Ag:9.08%) and vs. a different certified alloy of similar composition without Pt 11600 eV > Pt(U_L3)=11564 eV



Courtesy of A.G.Karydas, (National Center for Scientific Research "Demokritos", Greece) School on Synchrotron Light Sources and their Applications, 13-24 January 2025

Joint IAEA-Elettra training





Annual Training Workshop on Synchrotron Technologies and Techniques and their Applications and and a state of the state of

21 - 25 Oct 2024

Objectives

Trieste, Italy Event code: EVT2304289

 XRF XAFS MCX

To allow people with no or limited experience in synchrotron light experiments to participate in hands-on experiments and training at different beamlines, as well as to learn how to write successful proposal applications in order to be able to secure beamtime for themselves. The training will include experimental activities at the following beamlines operating at Elettra Sincrotrone Trieste:

Related resources

- Information Sheet
- Participation Form (Form A)
- Grant Application Form (Form C)

The next training will be announced soon and will be held in the period 26-30 May 2025 SISSI beamline (FTIR microscopy) will replace MCX beamline (X-ray diffraction)



Thanks for your attention!

Alessandro Migliori <u>a.migliori@iaea.org</u>

https://nucleus-new.iaea.org/sites/nuclear-instrumentation/Pages/Home.aspx https://www.elettra.trieste.it/lightsources/elettra/elettra-beamlines/microfluorescence/x-ray-fluorescence.html